

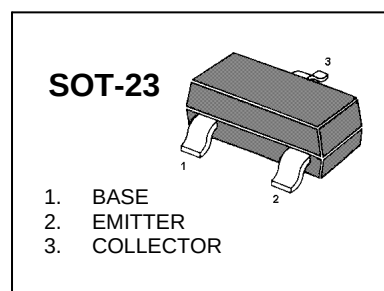
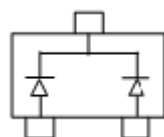
Plastic-Encapsulate Diodes

SWITCHING DIODES

FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

MARKING: A4



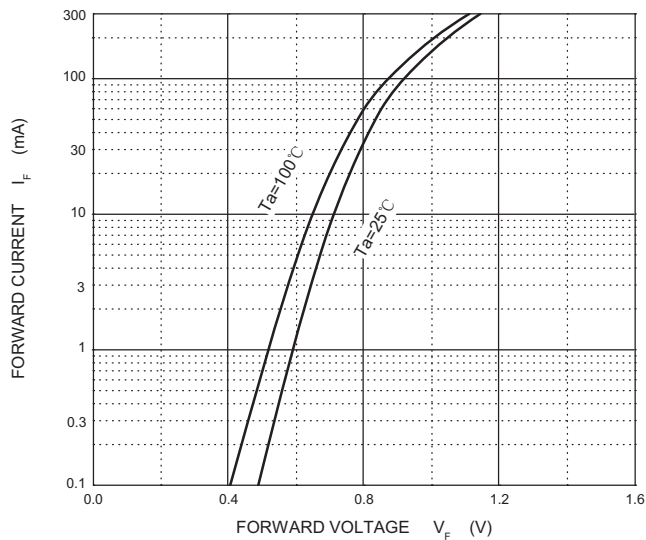
Maximum Ratings @Ta=25°C

Parameter	Symbol	Limit	Unit
Reverse Breakdown Voltage	V_{RM}	70	V
DC Blocking Voltage	V_R	70	V
Forward Current	I_F	200	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	2.0	A
Power Dissipation	P_D	225	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature range	T_{STG}	-55~+150	°C

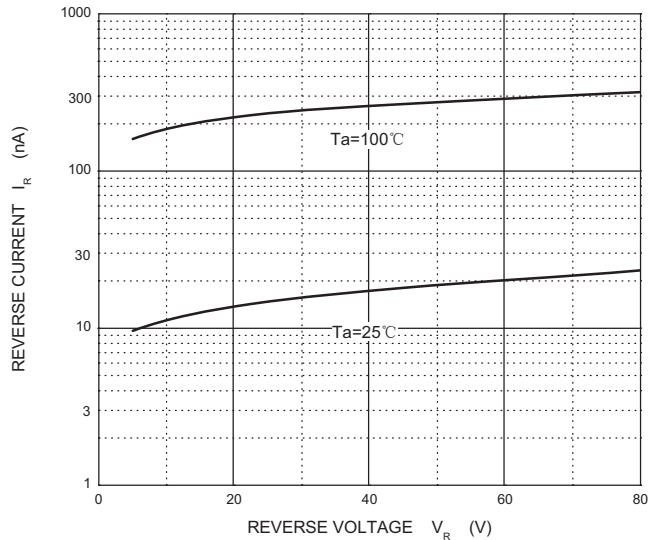
Electrical Characteristics @Ta=25°C

Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	V_R	70			V	$I_R=100\mu A$
Forward voltage	V_{F1}			0.715	V	$I_F=1mA$
	V_{F2}			0.855	V	$I_F=10mA$
	V_{F3}			1	V	$I_F=50mA$
	V_{F4}			1.25	V	$I_F=150mA$
Reverse current	I_R			2.5	μA	$V_R=70V$
Capacitance between terminals	C_T			1.5	pF	$V_R=0, f=1MHz$
Reverse recovery time	t_{rr}			6	ns	$I_F = I_R = 10mA,$ $I_{rr} = 0.1 \times I_R, R_L = 100\Omega$

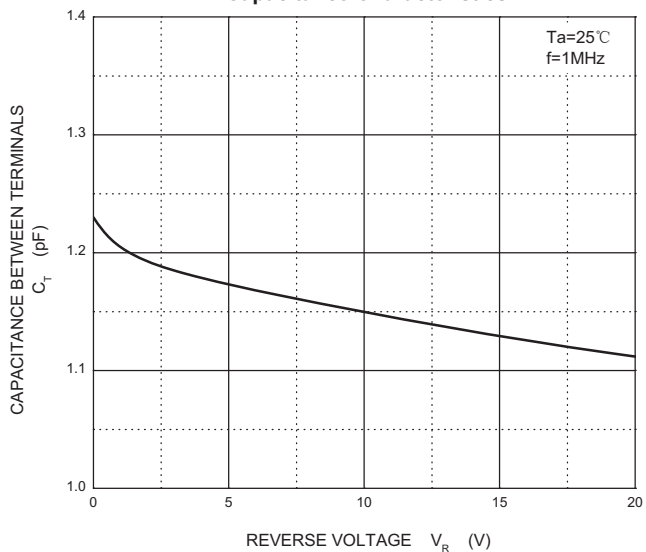
Forward Characteristics



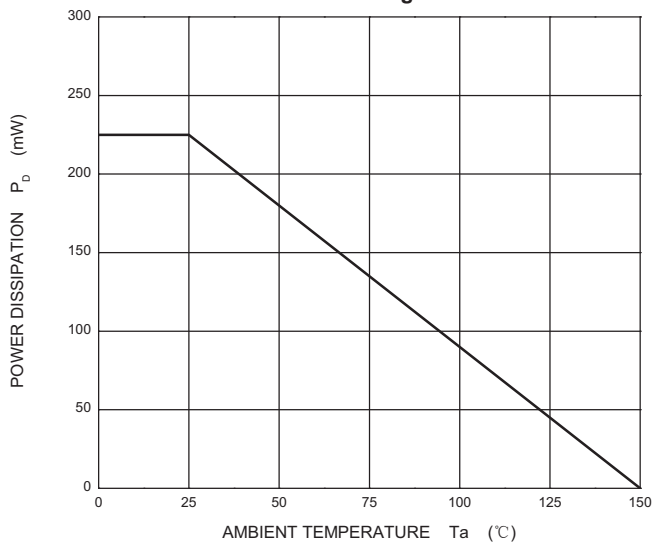
Reverse Characteristics



Capacitance Characteristics



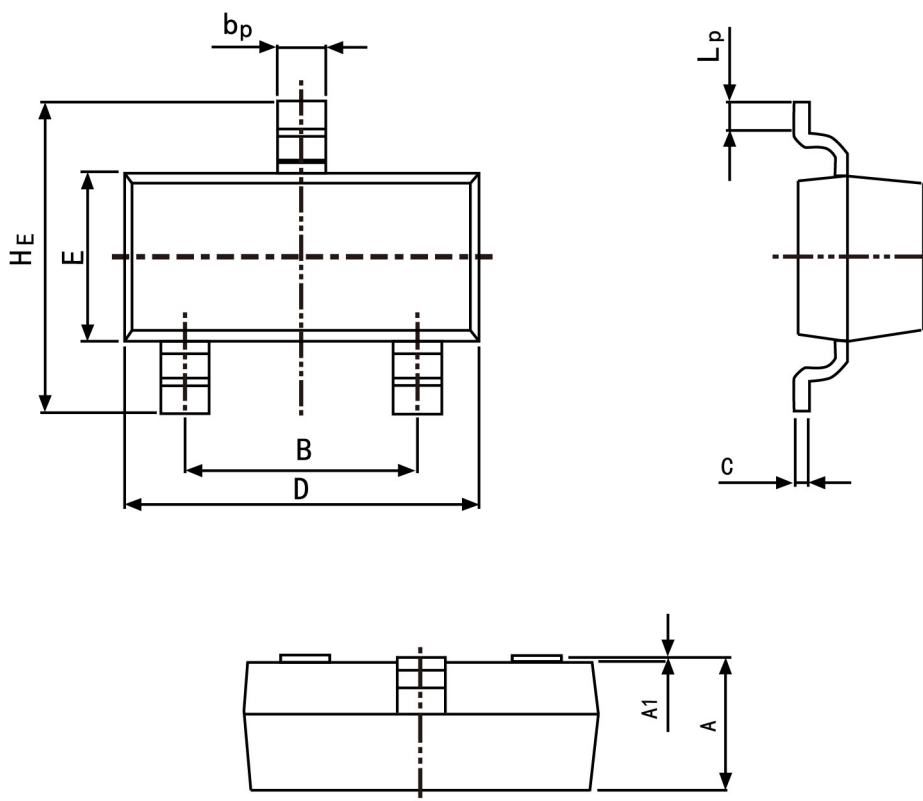
Power Derating Curve



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.40
B	1.78	2.04
bp	0.35	0.50
C	0.08	0.19
D	2.70	3.10
E	1.20	1.65
HE	2.20	3.00
A1	0.100	0.013
Lp	0.20	0.50